



IN THE CLAIMS:

Claim 16 has been amended as follows:

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1           16. (Amended) A semiconductor device having a semiconductor chip,  
2           first electrodes formed on said semiconductor chip,  
3           barrier metals formed on said first electrodes and having laminated structures, and  
4           a plurality of second protruded electrodes, which serve as external connection terminals, formed  
5           on said barrier metals, wherein said barrier metals comprising:  
6                   a lowermost conductive metal layer laminated on said first electrodes, said lowermost  
7           conductive metal layer having a joining property with said first electrodes;  
8                   an intermediate conductive metal layer laminated on said lowermost conductive metal layer,  
9           said intermediate conductive metal layer being made of nickel (Ni); and  
10                   an uppermost conductive metal layer laminated on said ~~one or more~~ intermediate  
11           conductive metal ~~layers~~ layer, said uppermost conductive metal layer being made of a material which easily  
12           alloys with ~~the material~~ the nickel of said intermediate conductive metal ~~layers~~ layer and which has  
13           resistance to oxidation, said uppermost conductive metal layer being made of a metal selected from the  
14           group consisting of ~~gold (Au)~~, platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or of an alloy  
15           containing a metal selected from the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag)  
16           and rhodium (Rh).